

/ Descriptions

KF \$0) CD E GE Silicon NPN transistor in a TO-92LM Plastic Package.

/ Features

: \$9
High Collector-Base Voltage, high Current Gain Bandwidth Product.

/ Applications

High voltage power amplifier.

/ Equivalent Circuit



/ Pinning



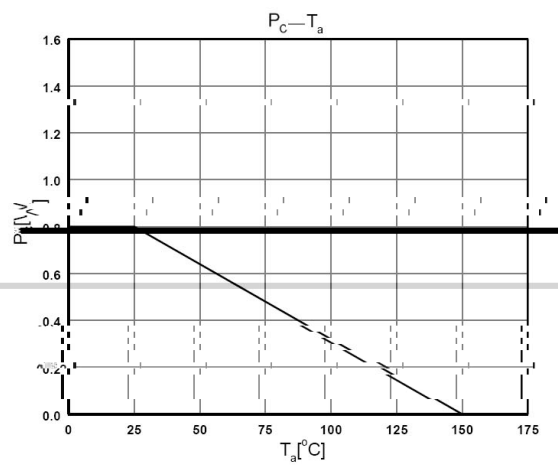
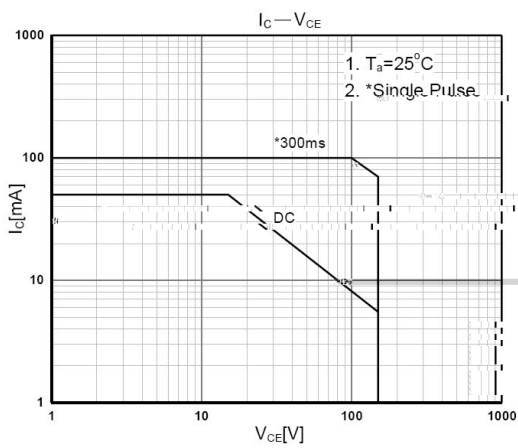
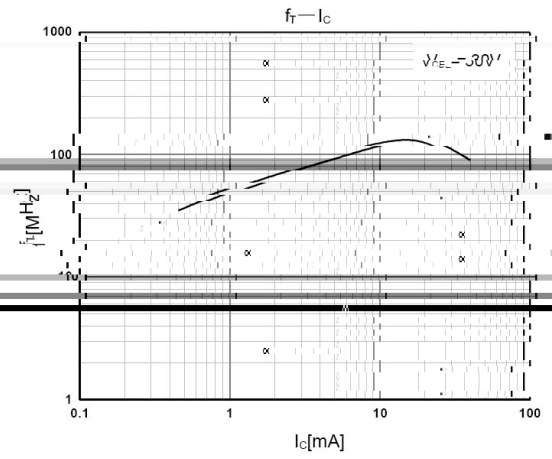
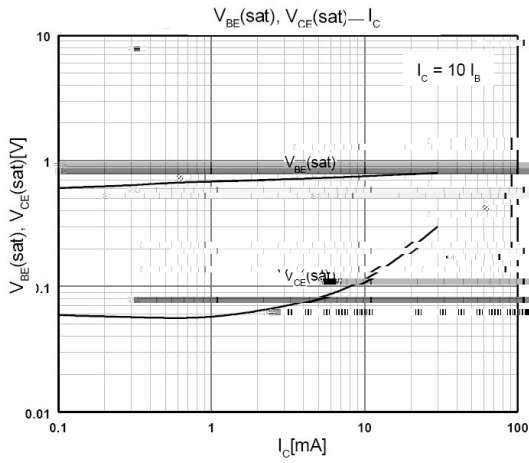
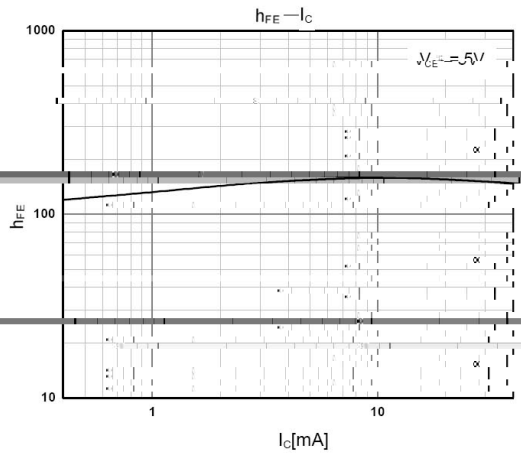
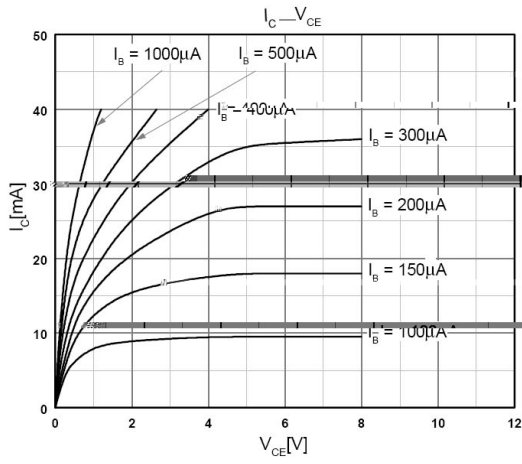
PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	R	O	Y
h _{FE} Range	40 80	70 140	120 240

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	150	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	50	mA
Collector Power Dissipation	P_C	1800	mW

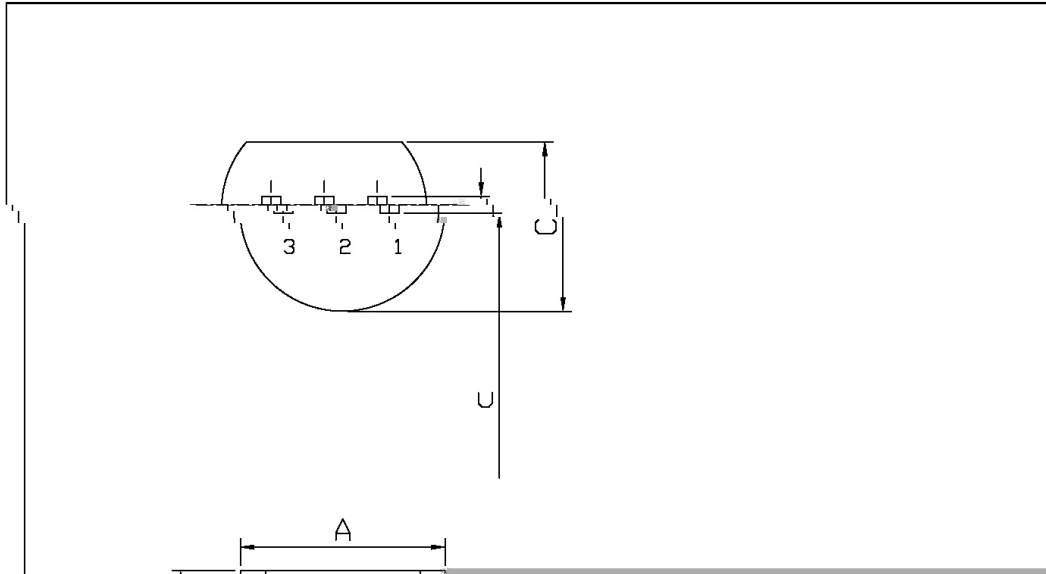
/ Electrical Characteristic Curve



/ Package Dimensions

TO-92LM

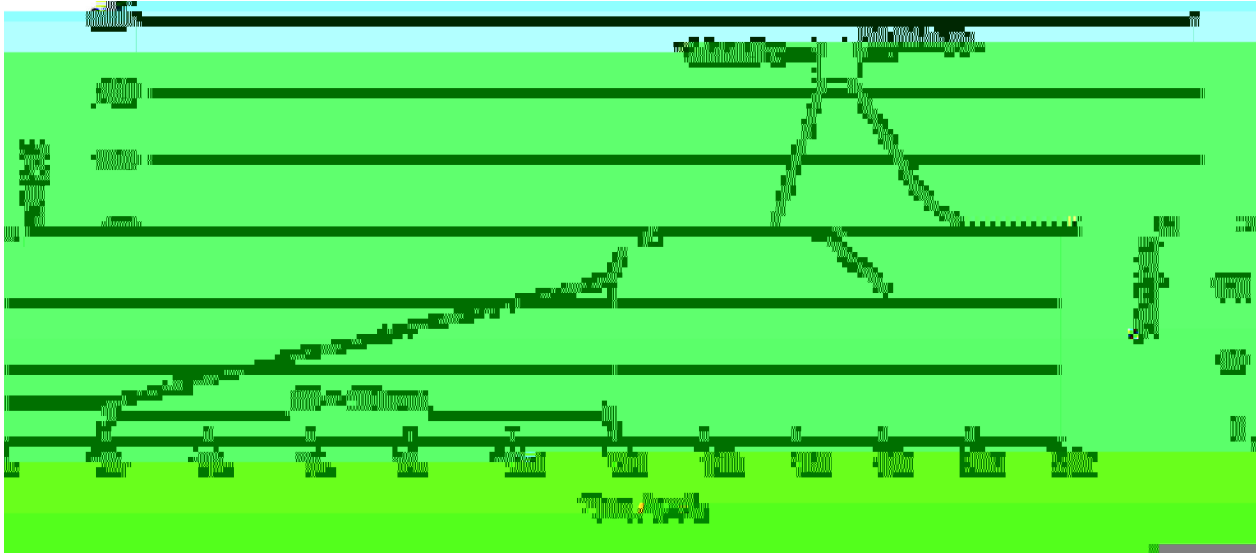
Unit: mm



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.47	5.1
C	1.27	1.52
E	0.51	0.76
E1	0.25	0.51
U	0.51	0.76

KSC2310
Rev.E Mar.-2016

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | |
|---|--------|------------|---|
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | 5..0.5sec; | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10...1 sec. Temp.:270±5℃ Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只纸带	纸带盒	纸带层盒	盒箱	只箱	盒	箱
							小箱 大箱

/ Notices